

6/08 as being a non-compliant abstract amendment

AMENDMENTS TO THE SPECIFICATION ABSTRACT

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On page ~~1~~, please replace the whole paragraph beginning on line 4 as following:

5 A dynamic random access memory (DRAM) is formed on a semiconductor wafer including a substrate, a thin film layer positioned on the substrate, and a photoresist layer positioned on the thin film layer. A first exposure process is performed to form first exposure regions including a plurality of lines
10 parallel to each other and covering each storage node. A second exposure process is performed to form second exposure regions cutting the plurality of lines of the first exposure regions that are rectangles interlaced with and perpendicular to each other on the photoresist layer and do not overlap the first
15 exposure regions. The first exposure regions and the second exposure regions of the photoresist layer are then removed for forming an array photoresist layer on the thin film layer, and ~~The array photoresist layer~~ functions as a mask to perform an etching process to the thin film layer for forming an array thin film layer
20 as a storage nodes in the DRAM.